

CMOS Strobed Hex Inverter/Buffer

High-Voltage Types (20-Volt Rating)

■ CD4502B consists of six inverter/buffers with 3-state outputs. A logic "1" on the OUTPUT DISABLE input produces a high-impedance state in all six outputs. This feature permits common bussing of the outputs, thus simplifying system design. A Logic "1" on the INHIBIT input switches all six outputs to logic "0" if the OUTPUT DISABLE input is a logic "0". This device is capable of driving two standard TTL loads, which is equivalent to six times the JEDEC "B"-series I_{OL} standard.

The CD4502B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic package (E suffix), 16-lead small-outline package (NSR suffix), and in chip form (H suffix). This device is similar to the MC14502.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to V_{DD} +0.5V

DC INPUT CURRENT, ANY ONE INPUT $\pm 10\mu A$

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ C$ to $+100^\circ C$ 500mW

For $T_A = +100^\circ C$ to $+125^\circ C$ Derate Linearly at 12mW/ $^\circ C$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW

OPERATING-TEMPERATURE RANGE (T_A) $-55^\circ C$ to $+125^\circ C$

STORAGE TEMPERATURE RANGE (T_{stg}) $-65^\circ C$ to $+150^\circ C$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10s max $+265^\circ C$

Features:

- 2 TTL-load output drive capability
- 3-state outputs
- Common output-disable control
- Inhibit control
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of $1\mu A$ at 18 V over full package-temperature range; 100 nA at 18 V and $25^\circ C$
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"
- Noise margin (full package-temperature range) =

1 V at $V_{DD} = 5 V$
2 V at $V_{DD} = 10 V$
2.5 V at $V_{DD} = 15 V$

Applications:

- 3-state hex inverter for interfacing IC's with data buses
- COS/MOS to TTL hex buffer

CD4502B Types

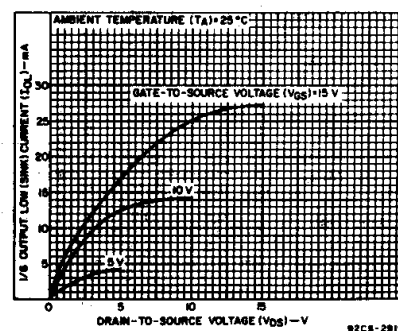
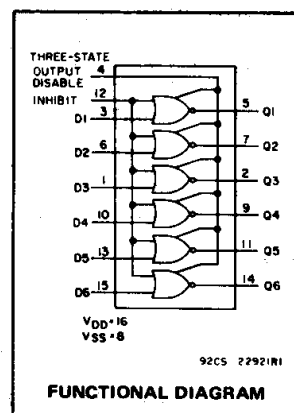


Fig.2 – Typical output low (sink) current characteristics.

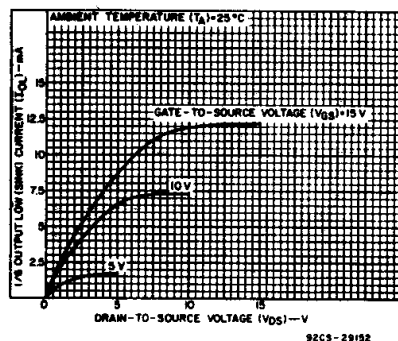


Fig.3 – Minimum output low (sink) current characteristics.

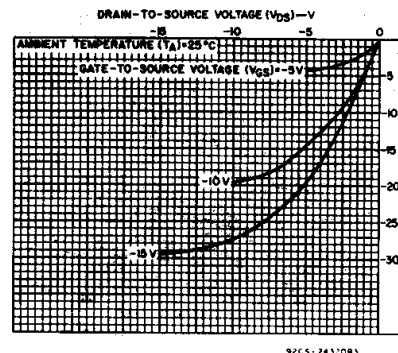


Fig.4 – Typical output high (source) current characteristics.

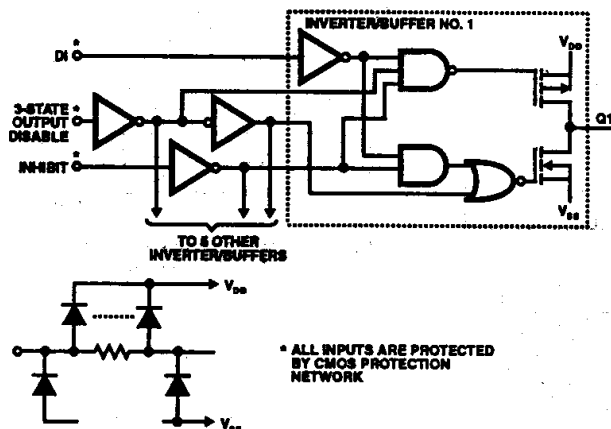
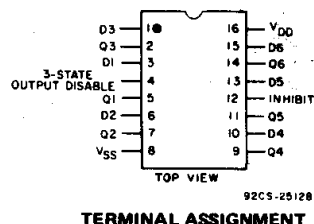


Fig.1 – Logic diagram of 1 of 6 identical inverter/buffers.



TRUTH TABLE			
DISABLE	INHIBIT	Dn	Qn
0	0	0	1
0	0	1	0
0	1	X	0
1	X	X	Z

Logic 0 = Low
Z = High Impedance
X = Don't Care
Logic 1 = High

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4502B Types

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)					+25			
				-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0,5	5	1	1	30	30	—	0.02	1	μA
	—	0,10	10	2	2	60	60	—	0.02	2	
	—	0,15	15	4	4	120	120	—	0.02	4	
	—	0,20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	3.84	3.66	2.52	2.16	3.06	6	—	mA
	0.5	0,10	10	9.6	9	6.6	5.4	7.8	15.6	—	
	1.5	0,15	15	25.2	24	16.8	14.4	20.4	40.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	0.5, 4.5	—	5	1.5				—	—	1.5	V
	1, 9	—	10	3				—	—	3	
	15, 13.5	—	15	4				—	—	4	
Input High Voltage, V _{IH} Min.	4.5	—	5	3.5				3.5	—	—	V
	9	—	10	7				7	—	—	
	13.5	—	15	11				11	—	—	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA
3-State Output Leakage Current I _{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	—	±10 ⁻⁴	±0.4	μA

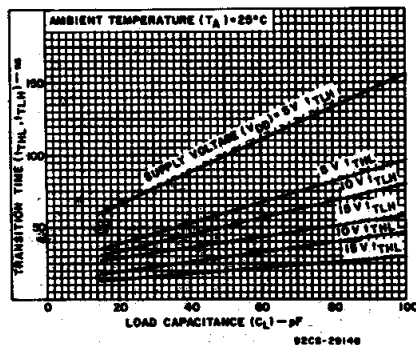


Fig. 8 - Typical transition time as a function of load capacitance.

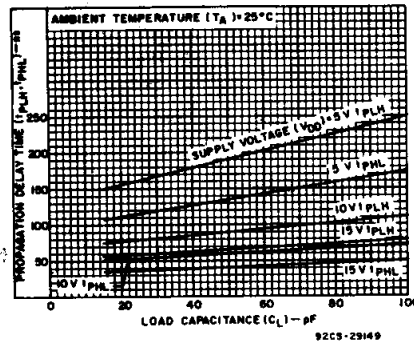


Fig. 9 - Typical propagation delay time as a function of load capacitance.

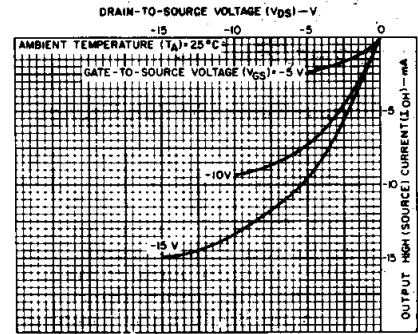


Fig. 5 - Minimum output high (source) current characteristics.

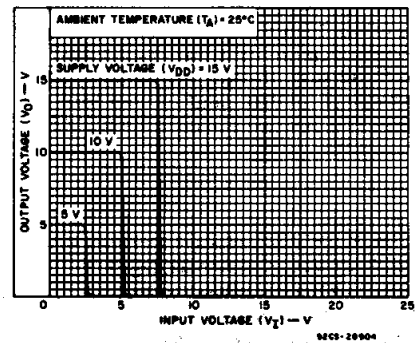


Fig. 6 - Typical voltage transfer characteristics.

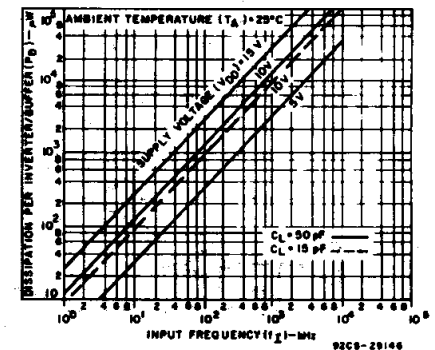


Fig. 7 - Typical power dissipation as a function of input frequency.

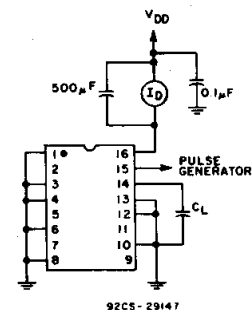


Fig. 10 - Power-dissipation test circuit.

CD4502B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20 \text{ ns}$,
 $C_L = 50 \text{ pF}$, $R_L = 200 \text{ K}\Omega$ Unless otherwise specified.

CHARACTERISTIC	TEST CONDITIONS	LIMITS			UNITS	
		VDD (V)	TYP	MAX		
Data or Inhibit Delay Times: High to Low, t _{PHL}		5	135	270	ns	
		10	60	120		
		15	40	80		
Low to High, t _{PLH}		5	190	380		
		10	90	180		
		15	65	130		
Disable Delay Times: R _L =1 KΩ Output High to High Impedance, t _{PHZ}	See Fig. 14	5	60	120	ns	
		10	40	80		
		15	30	60		
High-Impedance to Output High, t _{PZH}		5	110	220		
		10	50	100		
		15	40	80		
Output Low to High Impedance, t _{PLZ}		5	125	250		
		10	65	130		
		15	55	110		
High Impedance to Output Low, t _{PZL}		5	125	250		
		10	55	110		
		15	40	80		
Transition Times: Low to High, t _{TLH}			5	100	200	ns
			10	50	100	
			15	40	80	
High to Low, t _{THL}		5	60	120		
		10	30	60		
		15	20	40		
Input Capacitance, C _{IN}	Any Input	5	7.5	pF		
Output Capacitance, C _{OUT}		7-8	15	pF		

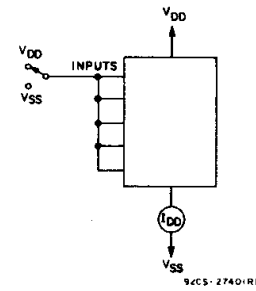


Fig. 11 - Quiescent-device-current test circuit.

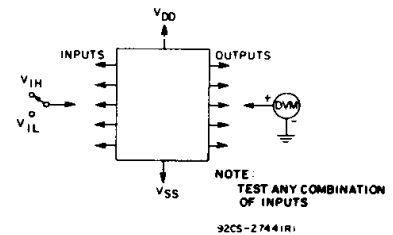


Fig. 12 - Input-voltage test circuit.

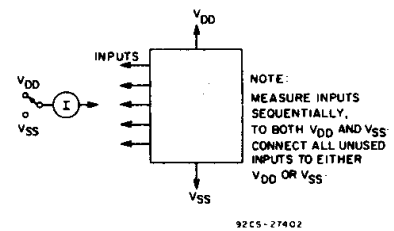


Fig. 13 - Input leakage current test circuit.

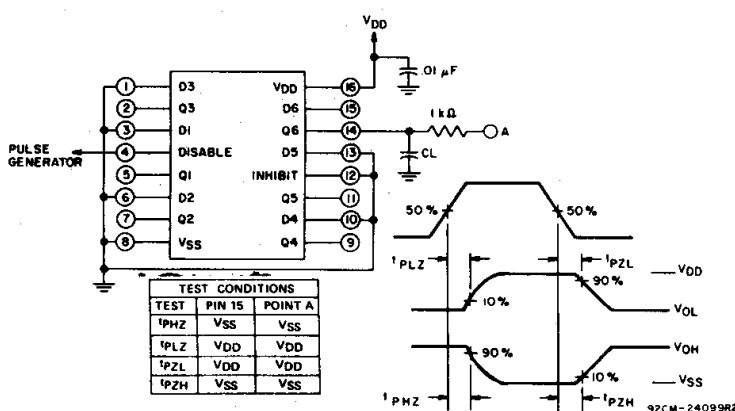
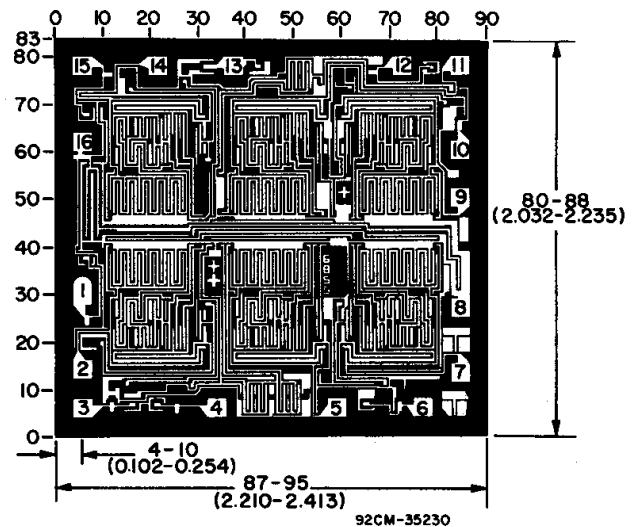


Fig. 14 - Disable delay times test circuit and waveforms.



Dimensions and Pad Layout for CD4502BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Mailing Address:

Texas Instruments
Post Office Box 655303
Dallas, Texas 75265